

**FACULTY OF INFORMATICS**  
**B.E. 4/4 (IT) I Semester (Main) Examination, December 2011**  
**VLSI DESIGN**

Time : 3 Hours]

[Max. Marks : 75

**Note : Answer all questions from Part A. Answer any five questions from Part B.**

## PART – A

(25 Marks)



1. Present a general overview of the design hierarchy. 2
2. Sketch pFET AOI circuit and pFET OAI circuit using pFET rules for the following : 3  

$$X = \overline{(a \cdot b) + (c \cdot d)}$$

$$Y = \overline{(a + e) \cdot (b + f)}$$
3. List rules associated with stick diagram layout. 2
4. Sketch logic diagram and its layout for a non-inverting buffer. 3
5. Explain cell concept briefly. 2
6. Illustrate dependence of Midpoint voltage,  $V_m$  on the relative device sizes contained in  $(\beta_n / \beta_p)$  for a pFET. 3
7. Explain how increasing the device ratio decreases the output low voltage in a pseudo-nMOS. 2
8. Write the three states of a Tri-state circuit. Sketch CMOS circuit and state where Tri-state circuits are useful. 3
9. What is a Procedural Block in Behavioral modeling ? Write three types of Timing controls that are used in a Procedural Block. 2
10. What is an Initialization vector in CMOS testing ? How does this overcome missing a fault in testing ? 3

## PART – B

(50 Marks)

11. a) Illustrate Bubble pushing using DeMorgan rules. 4  
b) Discuss TG-based exclusive-OR and exclusive-NOR circuits. 6

12. a) Sketch a circuit and its Layer Patterning for a CMOS Not gate and trace the logic operation on layout. 4
- b) Illustrate the gate capacitance in an n-channel MOSFET using the term, Oxide capacitance. Present a simple linear model for a MOSFET as a linear resistor and derive an approximate equation for current flow. 6
13. a) Describe Lithography. 5
- b) Define Rise Time and Fall Time, and derive the equations for the same. 6
14. a) Describe a Dynamic logic gate using an example. 5
- b) Define Static Noise Margin. Explain writing 1 operation to a static RAM. 5
15. Describe VLSI. Design flow showing Chip-level physical design issues. 10
16. Discuss signal delay as a function of line length, interconnect delay and crosstalk issues in VLSI design. 10
17. Write short note on : 10
- a) Fabrication of CMOS ICS
- b) VLSI Design issues
- c) Testing of VLSI circuits.